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HM4887B-VB Datasheet

Dual P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	-100
$R_{DS(on)}$ max. (Ω) at V_{GS} = -10 V	0.110
$R_{DS(on)}$ max. (Ω) at V_{GS} = -4.5 V	0.155
Q_g typ. (nC)	5.65
I_D (A)	-4.5
Configuration	Single

FEATURES

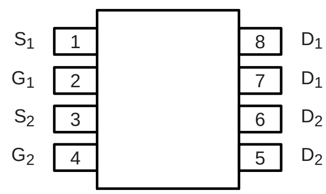
- Trench power MOSFET
- 100 % R_g and UIS tested

Pb-free
RoHS
COMPLIANT
HALOGEN
FREE

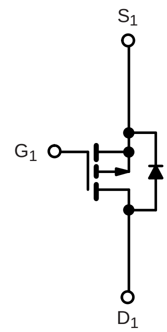
APPLICATIONS

- Active clamp in intermediate DC/DC power supplies
- LED Lighting
- Load switch

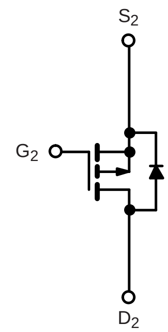
SO-8



Top View



P-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	-100	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current (T_J = 150 °C)	T_C = 25 °C	I_D	-4.5	A
	T_C = 70 °C		-3.6	
	T_A = 25 °C		-2.8 [b, c]	
	T_A = 70 °C		-2.1 [b, c]	
Pulsed drain current (t = 100 μs)		I_{DM}	-20	
Continuous source-drain diode current	T_C = 25 °C	I_S	-4.5[a]	
	T_A = 25 °C		-2.8[b, c]	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	-15	
Single pulse avalanche energy		E_{AS}	11.25	mJ
Maximum power dissipation	T_C = 25 °C	P_D	27.8	W
	T_C = 70 °C		17.8	
	T_A = 25 °C		3.5 [b, c]	
	T_A = 70 °C		2.2 [b, c]	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) [d, e]			260	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient [b, f]	t ≤ 10 s	R_{thJA}	29	36	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	3.6	4.6	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = -250 μA	-100	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	I_D = -250 μA	-	-63	-	mV/°C
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$		-	4.2	-	
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D =-250 μA	-1.1	-	-2.6	V
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = -100 V, V_{GS} = 0 V	-	-	-1	μA
		V_{DS} = -100 V, V_{GS} = 0 V, T_J = 70 °C	-	-	-10	
On-state drain current [a]	$I_{D(on)}$	V_{DS} ≥ -10 V, V_{GS} = -10 V	-15	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = -10 V, I_D = -3.8 A	-	0.110		Ω
		V_{GS} = -4.5 V, I_D = -3.2 A	-	0.155		
Forward transconductance [a]	g_{fs}	V_{DS} = -10 V, I_D = -3.8 A	-	8	-	S
Dynamic [b]						
Input capacitance	C_{iss}	V_{DS} = -50 V, V_{GS} = 0 V, f = 1 MHz	-	515	-	pF
Output capacitance	C_{oss}		-	162	-	
Reverse transfer capacitance	C_{rss}		-	10	-	
Total gate charge	Q_g	V_{DS} = -50 V, V_{GS} = -10 V, I_D = -3.8 A	-	10.9	16.5	nC
		V_{DS} = -50 V, V_{GS} = -4.5 V, I_D = -3.8 A	-	5.65	8.5	
Gate-source charge	Q_{gs}		-	1.7	-	
Gate-drain charge	Q_{gd}		-	2.5	-	
Gate resistance	R_g	f = 1 MHz	1.96	9.8	19.6	Ω
Turn-on delay time	$t_{d(on)}$	V_{DD} = -50 V, R_L = 16.1 Ω, I_D ≅ -3.1 A, V_{GEN} = -10 V, R_g = 1 Ω	-	10	20	ns
Rise time	t_r		-	22	40	
Turn-off delay time	$t_{d(off)}$		-	20	40	
Fall time	t_f		-	20	40	
Turn-on delay time	$t_{d(on)}$	V_{DD} = -50 V, R_L = 16.1 Ω, I_D ≅ -3.1 A, V_{GEN} = -4.5 V, R_g = 1 Ω	-	35	55	
Rise time	t_r		-	40	60	
Turn-off delay time	$t_{d(off)}$		-	22	40	
Fall time	t_f		-	1622	40	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	T_C = 25 °C	-	-	-16	A
Pulse diode forward current	I_{SM}		-	-	-15	
Body diode voltage	V_{SD}	I_S = -3.1 A, V_{GS} = 0 V	-	-0.8	-1.2	V
Body diode reverse recovery time	t_{rr}	I_F = -3.1 A, di/dt = 100 A/μs, T_J = 25 °C	-	43	65	ns
Body diode reverse recovery charge	Q_{rr}		-	80	120	nC
Reverse recovery fall time	t_a		-	36	-	ns
Reverse recovery rise time	t_b		-	7	-	

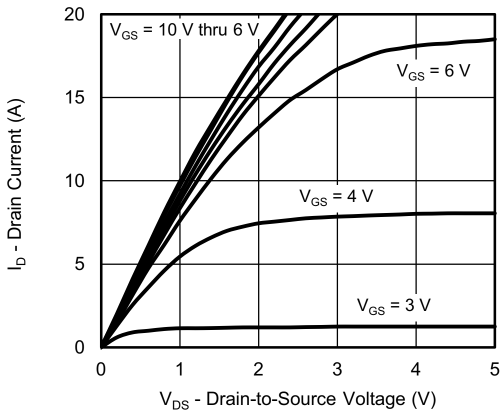
Notes

a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %

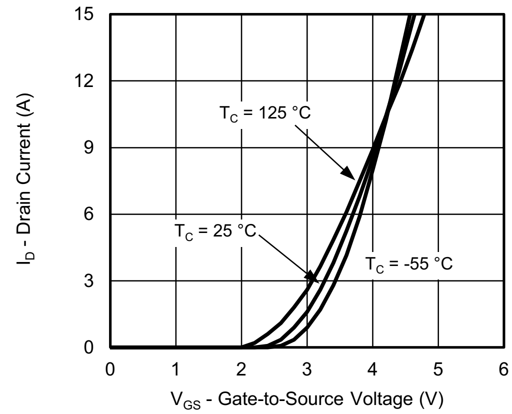
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

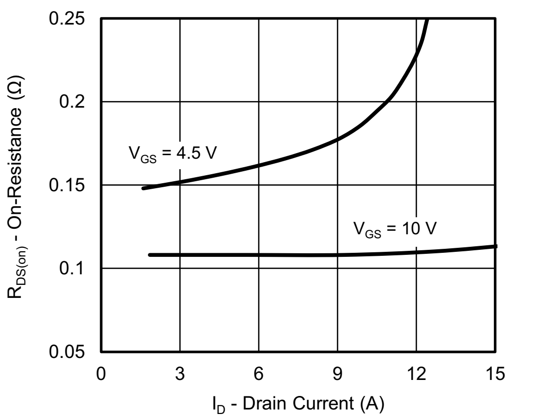
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



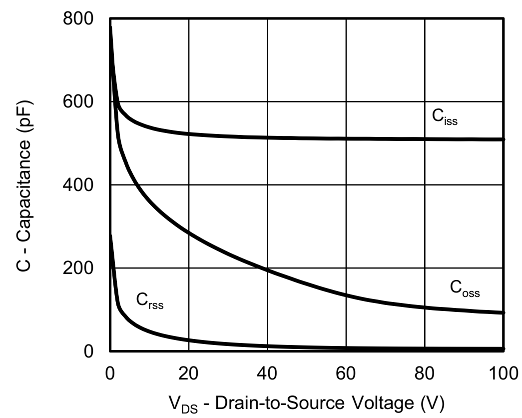
Output Characteristics



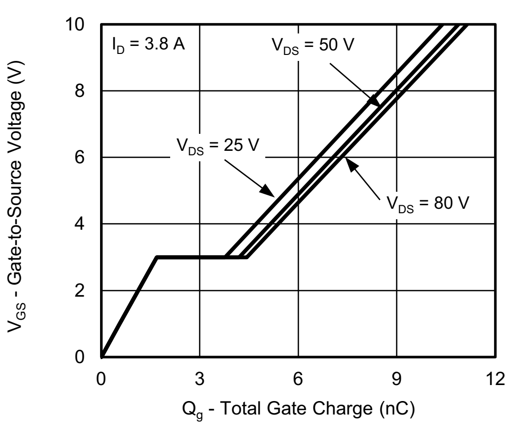
Transfer Characteristics



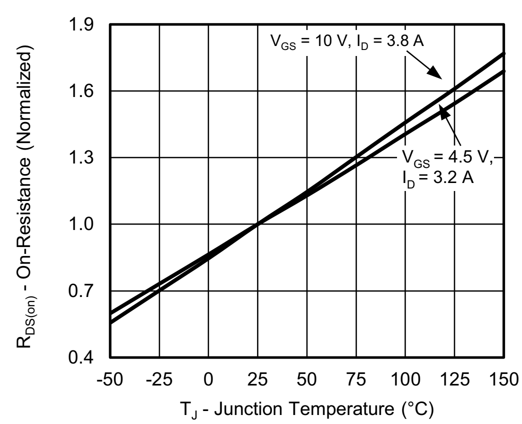
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

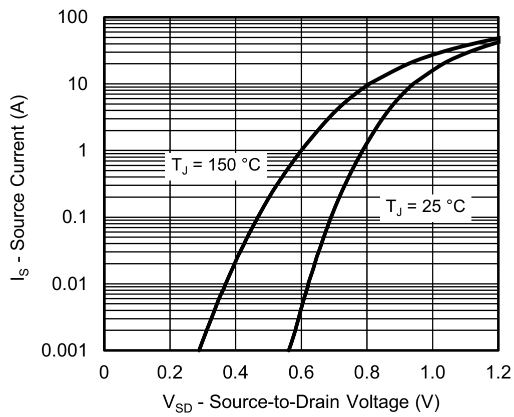


Gate Charge

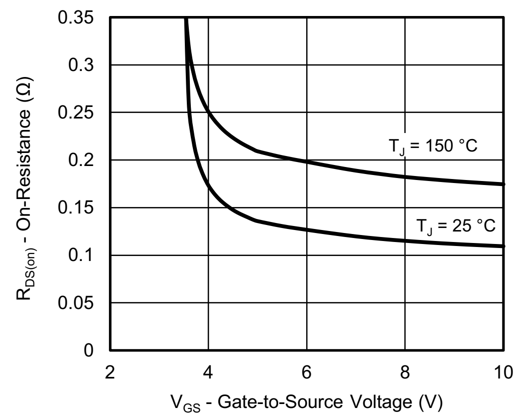


On-Resistance vs. Junction Temperature

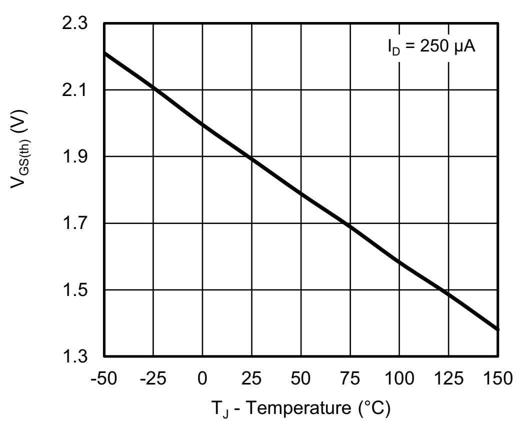
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



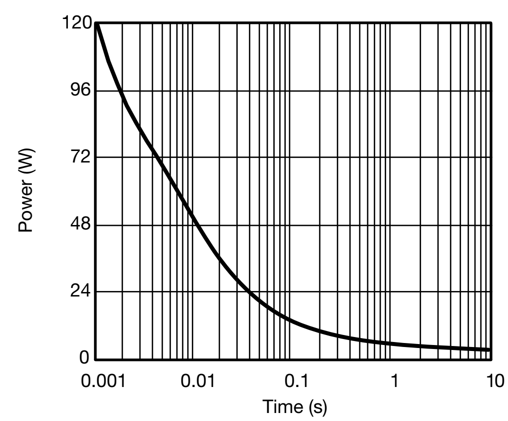
Source-Drain Diode Forward Voltage



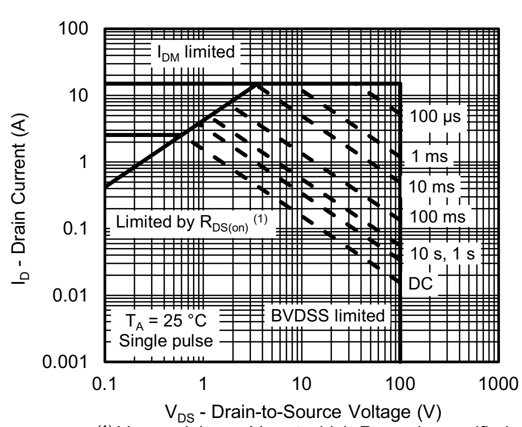
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



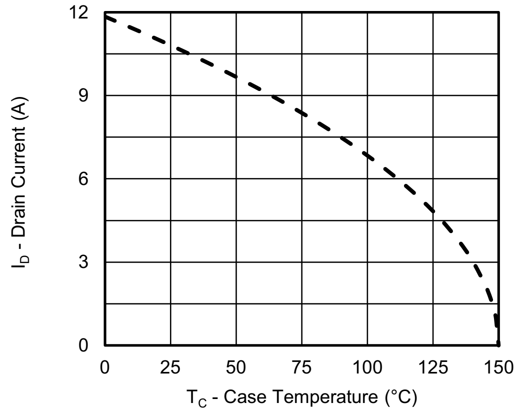
Single Pulse Power, Junction-to-Ambient



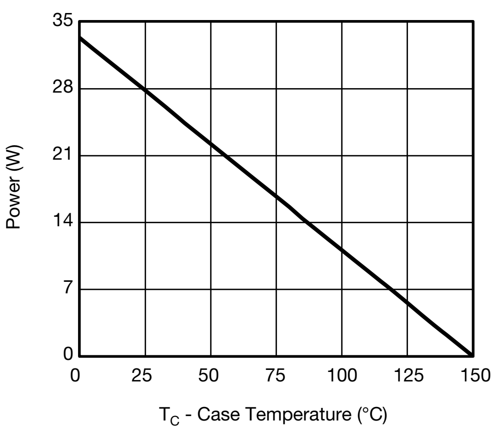
(1) V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

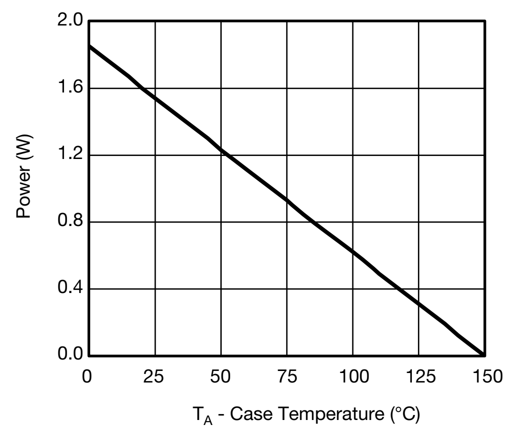
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating [a]



Power, Junction-to-Case

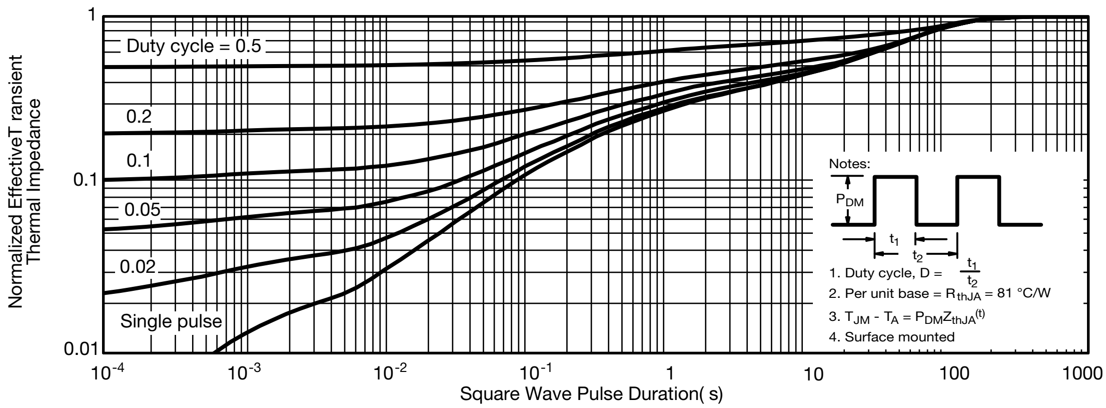


Power, Junction-to-Ambient

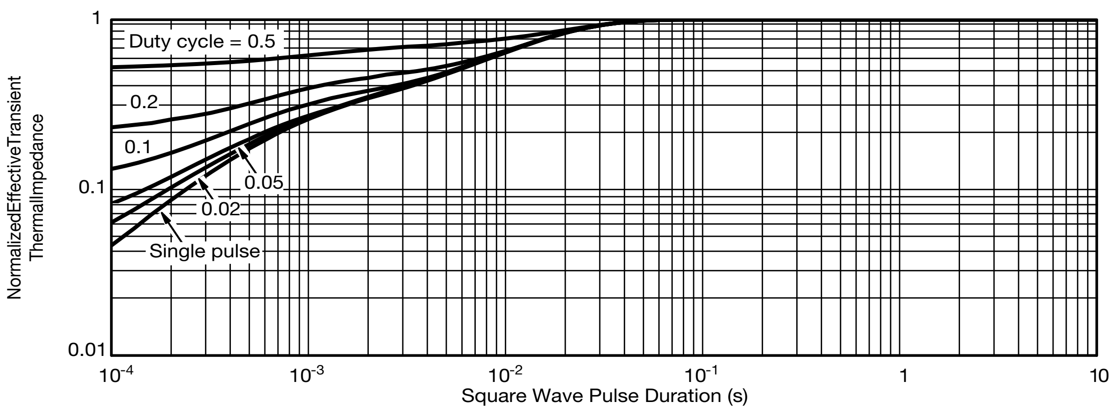
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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